

IN THE CLAIMS

This listing of claims replaces all prior listings:

1. (Currently Amended) A method of manufacturing a semiconductor device including a laser chip and a base having the laser chip mounted thereon, including the step of:
providing an assembly with the laser chip mounted on the base; and
irradiating the laser chip and base with an energy beam having a shorter wavelength than an oscillation wavelength of the laser chip to remove adherent from the laser chip and the base.
2. (Currently Amended) A method of manufacturing a semiconductor device according to claim 1 including the step of:
shutting offsealing the base from the outside, after the step of irradiating the laser chip and the base with the energy beam.
3. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein a laser chip having a nitride semiconductor layer is used as the laser chip.
4. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein a laser chip having an oscillation wavelength of 550 nm or less is used as the laser chip.
5. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein irradiation takes place using laser light or ultraviolet light as the energy beam.
6. (Original) A method of manufacturing a semiconductor device including a laser chip and a base, including the step of:
irradiating the base having the laser chip mounted thereon with plasma.
7. (Currently Amended) A method of manufacturing a semiconductor device according to claim 6 including the step of:
shutting offsealing the base from the outside, after the step of irradiating the base with the plasma.

8. (Original) A method of manufacturing a semiconductor device according to claim 6, wherein a laser chip having a nitride semiconductor layer is used as the laser chip.

9. (Original) A method of manufacturing a semiconductor device according to claim 6, wherein a laser chip having an oscillation wavelength of 550 nm or less is used as the laser chip.

10. (Original) A method of manufacturing a semiconductor device according to claim 6, wherein the step of irradiating the base with the plasma takes place in an atmosphere of oxygen.